H5N5006DL, H5N5006DS

Silicon N Channel MOS FET
High Speed Power Switching

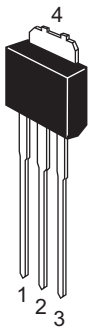
REJ03G0397-0100
Rev.1.00
May 30, 2006

Features

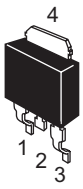
- Low on-resistance: $R_{DS(on)}$ = 2.5 Ω typ.
- Low leakage current: I_{DSS} = 1 µA max. (at V_{DS} = 500 V)
- High speed switching: t_f = 15 ns typ. (at V_{GS} = 10 V, V_{DD} ≅ 250 V, I_D = 1.5 A)
- Low gate charge: Qg = 14 nC typ. (at V_{DD} = 400 V, V_{GS} = 10 V, I_D = 3 A)
- Avalanche ratings

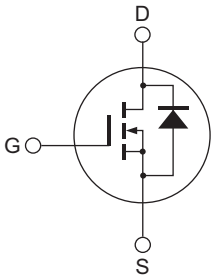
Outline

RENESAS Package code: PRSS0004ZD-B
(Package name: DPAK (L)-(2))



RENESAS Package code: PRSS0004ZD-C
(Package name: DPAK (S))





1. Gate
2. Drain
3. Source
4. Drain

Absolute Maximum Ratings

(Ta = 25°C)

Item	Symbol	Ratings	Unit
Drain to source voltage	V_{DSS}	500	V
Gate to source voltage	V_{GSS}	±30	V
Drain current	I_D	3	A
Drain peak current	$I_{D\ (pulse)}$ Note1	12	A
Body-drain diode reverse drain current	I_{DR}	3	A
Body-drain diode reverse drain peak current	$I_{DR\ (pulse)}$ Note1	12	A
Avalanche current	I_{AP} Note3	3	A
Channel dissipation	Pch Note2	30	W
Channel to case thermal impedance	θch-c	4.17	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	–55 to +150	°C

Notes: 1. PW ≤ 10 µs, duty cycle ≤ 1%
2. Value at Tc = 25°C
3. STch = 25°C, Tch ≤ 150°C

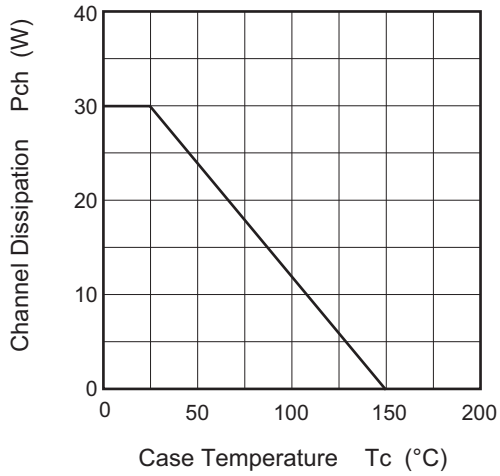
Electrical Characteristics

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Drain to source breakdown voltage	$V_{(BR)DSS}$	500	—	—	V	I_D = 10 mA, V_{GS} = 0
Zero gate voltage drain current	I_{DSS}	—	—	1	µA	V_{DS} = 500 V, V_{GS} = 0
Gate to source leak current	I_{GSS}	—	—	±0.1	µA	V_{GS} = ±30 V, V_{DS} = 0
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	—	4.5	V	V_{DS} = 10 V, I_D = 1 mA
Forward transfer admittance	$\|y_{fs}\|$	1.5	2.5	—	S	I_D = 1.5 A, V_{DS} = 10 V Note4
Static drain to source on state resistance	$R_{DS(on)}$	—	2.5	3.0	Ω	I_D = 1.5 A, V_{GS} = 10 V Note4
Input capacitance	Ciss	—	365	—	pF	V_{DS} = 25 V V_{GS} = 0 f = 1 MHz
Output capacitance	Coss	—	35	—	pF	
Reverse transfer capacitance	Crss	—	8	—	pF	
Turn-on delay time	$t_{d(on)}$	—	20	—	ns	V_{DD} ≅ 250 V, I_D = 1.5 A V_{GS} = 10 V R_L = 167 Ω Rg = 10 Ω
Rise time	t_r	—	12	—	ns	
Turn-off delay time	$t_{d(off)}$	—	48	—	ns	
Fall time	t_f	—	15	—	ns	
Total gate charge	Qg	—	14	—	nC	V_{DD} = 400 V V_{GS} = 10 V I_D = 3 A
Gate to source charge	Qgs	—	2	—	nC	
Gate to drain charge	Qgd	—	8	—	nC	
Body-drain diode forward voltage	V_{DF}	—	0.85	1.3	V	I_F = 3 A, V_{GS} = 0 Note4
Body-drain diode reverse recovery time	t_{rr}	—	270	—	ns	I_F = 3 A, V_{GS} = 0 di_F/dt = 100 A/µs
Body-drain diode reverse recovery charge	Q_{rr}	—	0.8	—	µC	

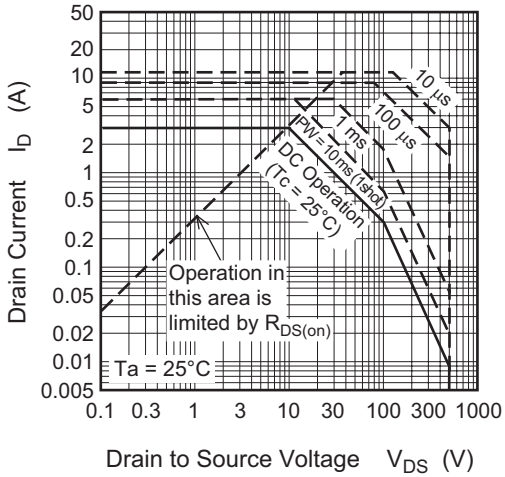
Notes: 4. Pulse test

Main Characteristics

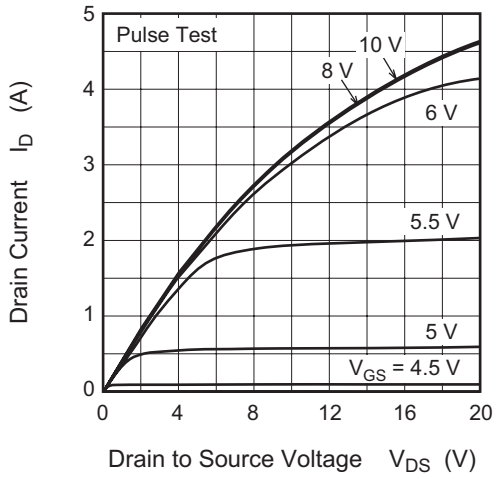
Power vs. Temperature Derating



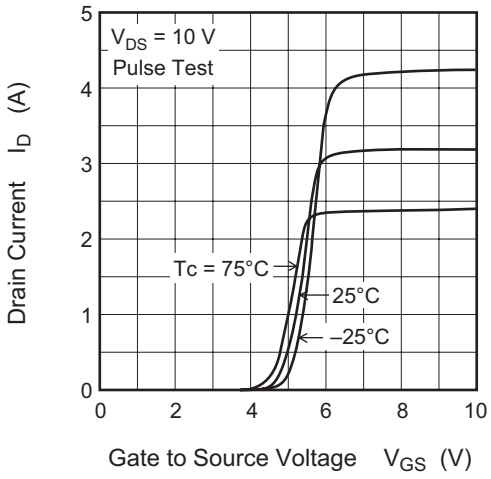
Maximum Safe Operation Area



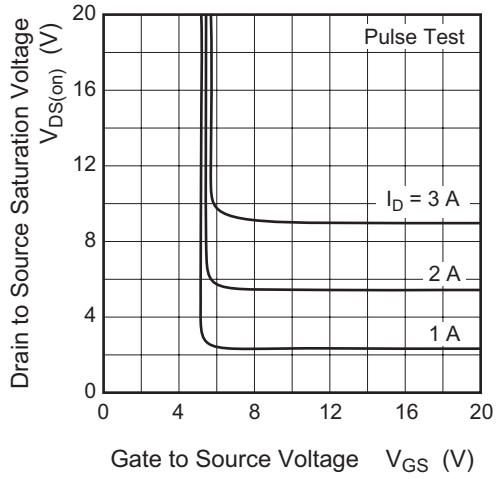
Typical Output Characteristics



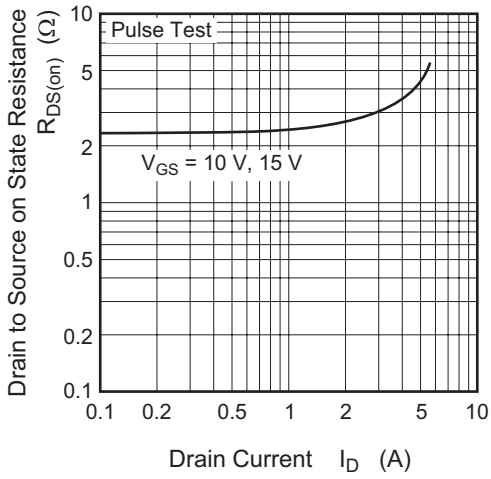
Typical Transfer Characteristics



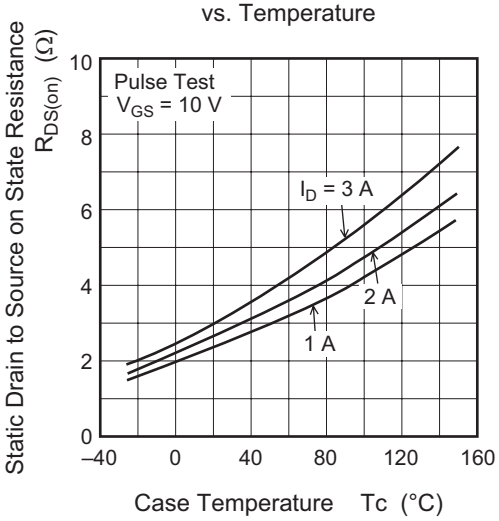
Drain to Source Saturation Voltage vs. Gate to Source Voltage



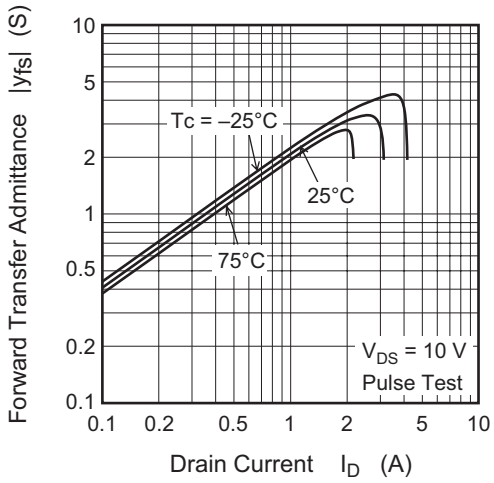
Static Drain to Source on State Resistance vs. Drain Current



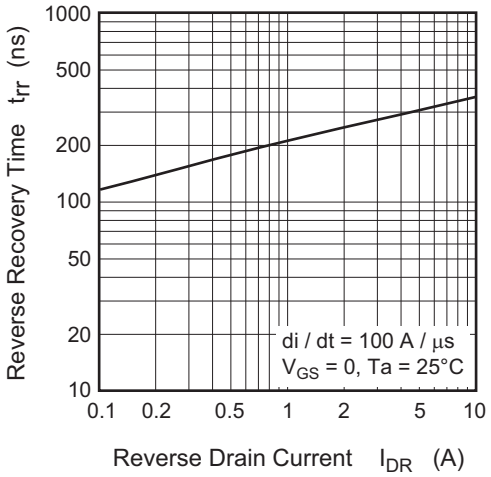
Static Drain to Source on State Resistance vs. Temperature



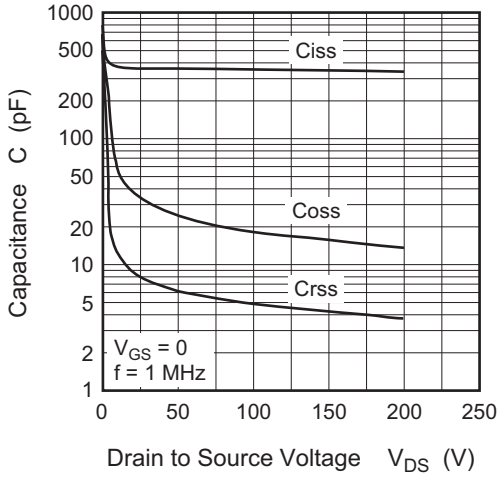
Forward Transfer Admittance vs. Drain Current



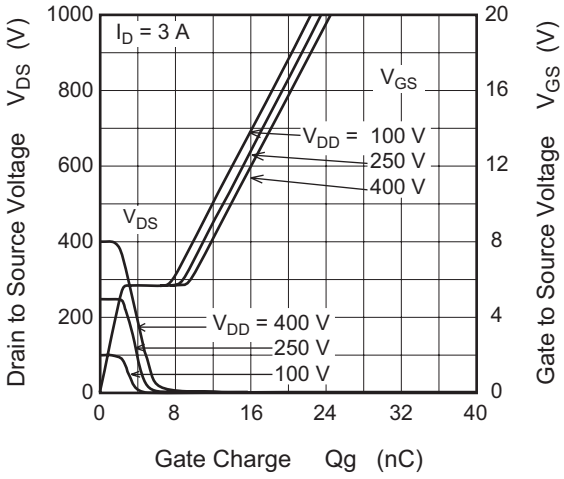
Body-Drain Diode Reverse Recovery Time



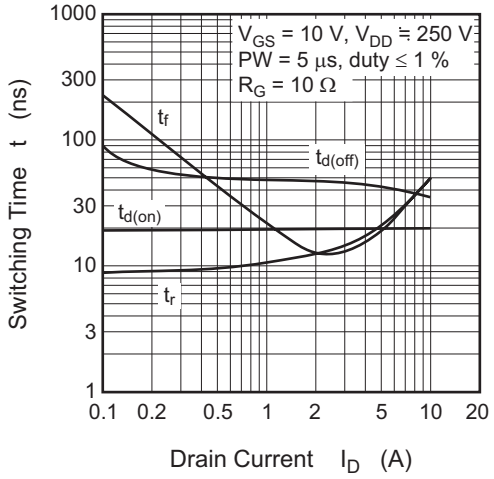
Typical Capacitance vs. Drain to Source Voltage



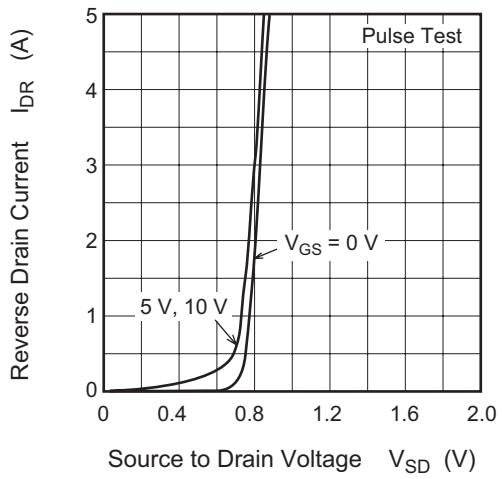
Dynamic Input Characteristics



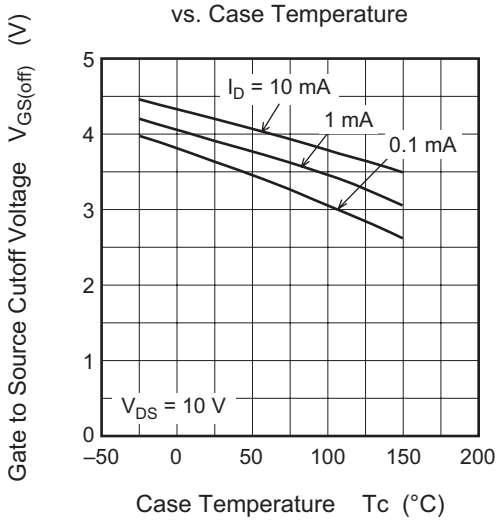
Switching Characteristics



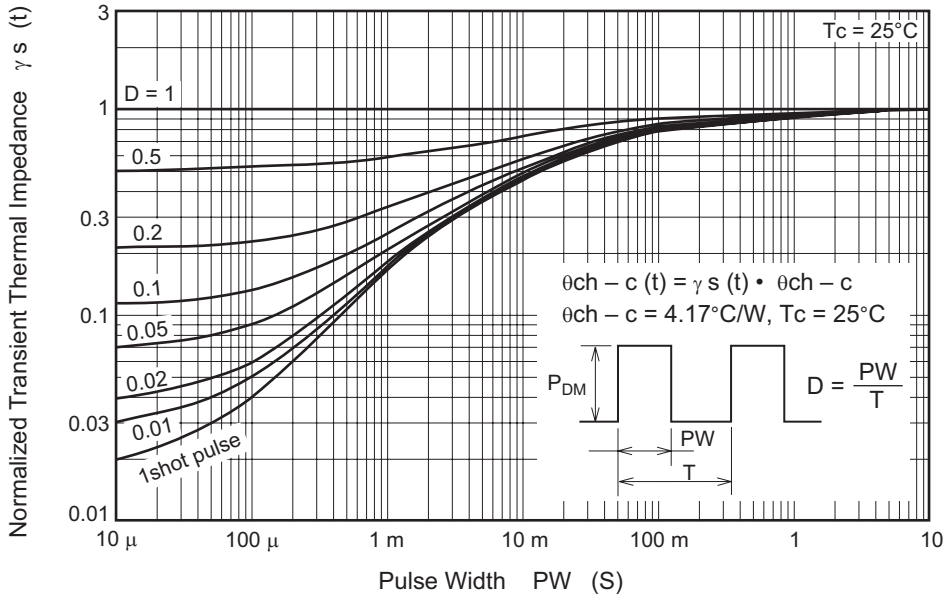
Reverse Drain Current vs.
Source to Drain Voltage



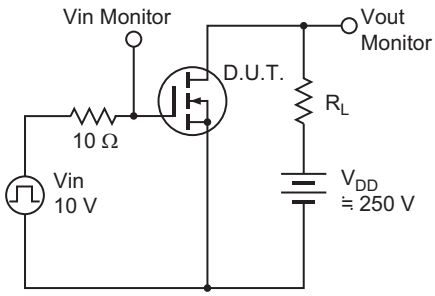
Gate to Source Cutoff Voltage
vs. Case Temperature



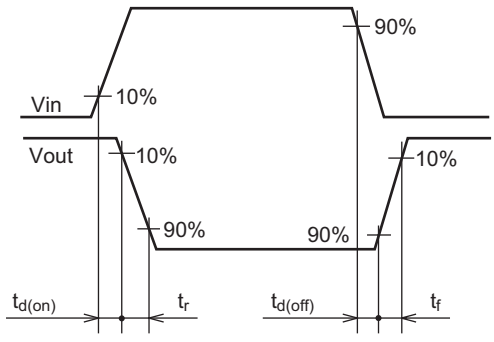
Normalized Transient Thermal Impedance vs. Pulse Width



Switching Time Test Circuit



Waveform

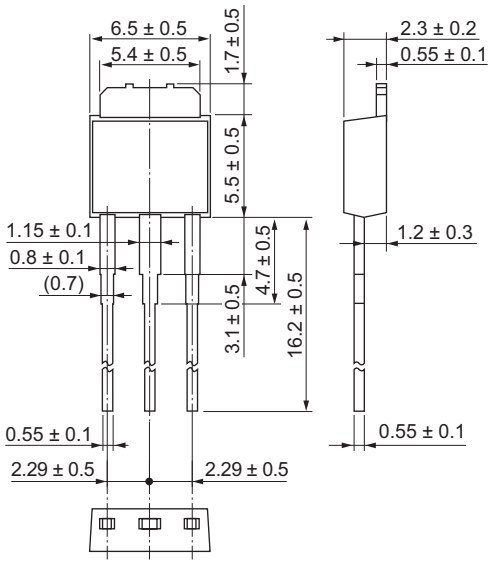


Package Dimensions

• H5N5006DL

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
DPAK(L)-(2)	—	PRSS0004ZD-B	DPAK(L)-(2) / DPAK(L)-(2)V	0.42g

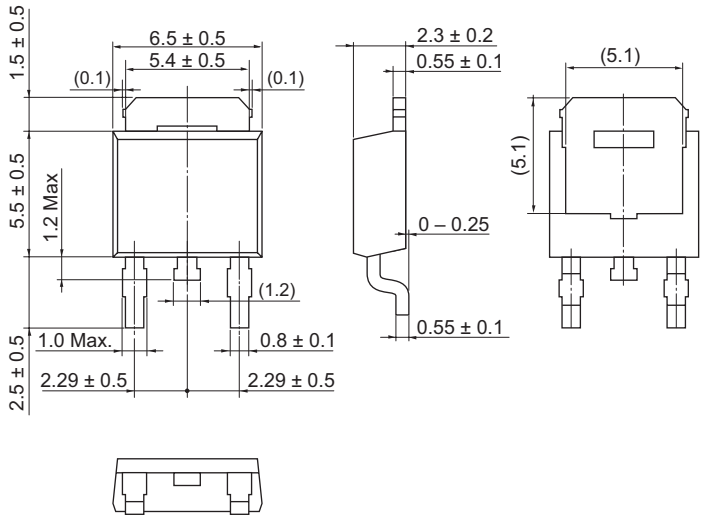
Unit: mm



• H5N5006DS

Package Name	JEITA Package Code	RENESAS Code	Previous Code	MASS[Typ.]
DPAK(S)	SC-63	PRSS0004ZD-C	DPAK(S) / DPAK(S)V	0.28g

Unit: mm



Ordering Information

Part Name	Quantity	Shipping Container
H5N5006DL-E	3200 pcs	Box (Sack)
H5N5006DSTL-E	3000 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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